

Dual N-channel 40 V, 5.8 m $\Omega$  standard level MOSFET

6 November 2013

Product data sheet

### 1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with  $V_{GS(th)}$  of greater than 1 V at 175  $^\circ\text{C}$

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qu	lick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	-	40	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	68	W
Static charac	cteristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 11		-	4.8	5.8	mΩ
Dynamic cha	aracteristics FET1 and FE	T2					
Q <sub>GD</sub>	gate-drain charge	$I_D = 20 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	10.5	-	nC

[1] Continuous current is limited by package.

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D1 D1 D2 D2
2	G1	gate1		
3	S2	source2		
4	G2	gate2	$\bigcirc$	
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

# 6. Ordering information

Table 3.Ordering in	formation					
Type number	Package	age				
	Name	Description	Version			
BUK7K6R2-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K6R2-40E	76E240

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; Tmb = 25 °C; <u>Fig. 1</u>	[1]	-	40	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	40	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	308	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	68	W
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# **BUK7K6R2-40E**

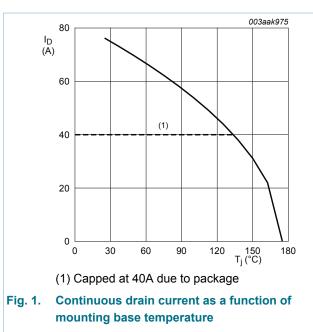
#### Dual N-channel 40 V, 5.8 mΩ standard level MOSFET

Symbol	Parameter	Conditions		Min	Max	Unit	
T <sub>stg</sub>	storage temperature			-55	175	°C	
Tj	junction temperature			-55	175	°C	
Source-drain diode FET1 and FET2							
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	40	А	
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	308	А	
Avalanche Ruggedness FET1 and FET2							
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_{D} &= 40 \text{ A};  \text{V}_{\text{sup}} \leq 40 \text{ V};  \text{V}_{\text{GS}} = 10 \text{ V}; \\ \text{T}_{j(\text{init})} &= 25 ^{\circ}\text{C};  \underline{\text{Fig. } 3} \end{split}$	[2][3]	-	157	mJ	

[1] Continuous current is limited by package.

[2] Refer to application note AN10273 for further information

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



 $V_{GS} \ge 10V$ 

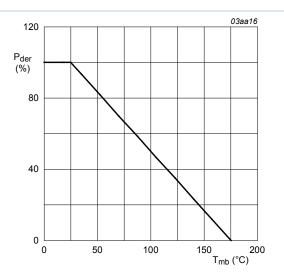
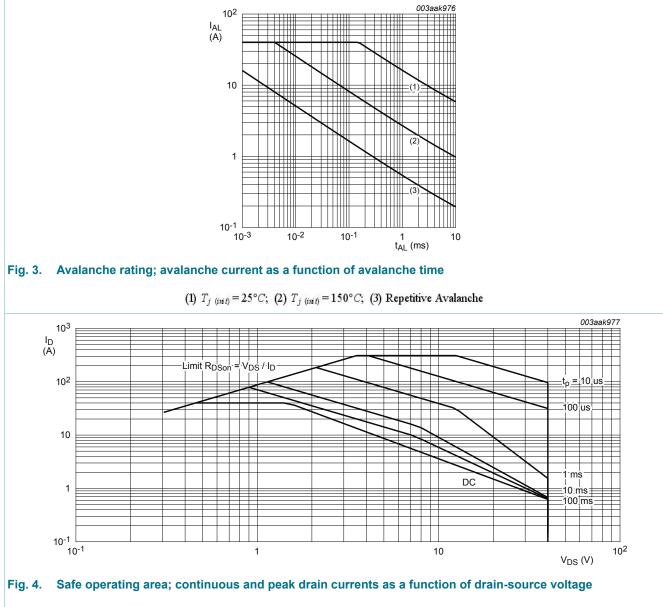


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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 $T_{mb} = 25^{\circ}C; \ I_{DM}$  is a single pulse

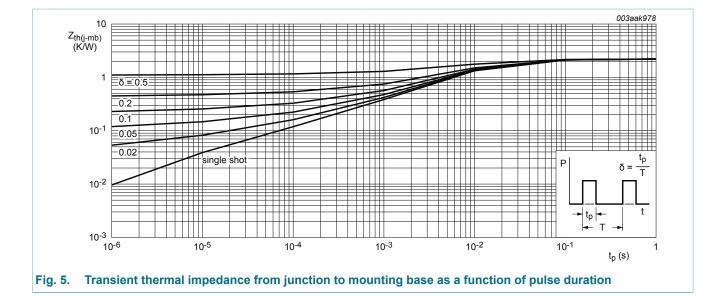
### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	2.21	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

#### Table 6. Thermal characteristics

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#### Dual N-channel 40 V, 5.8 m $\Omega$ standard level MOSFET



### **10.** Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2					_
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 9; Fig. 10	1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 9; Fig. 10	-	-	4.5	V
I <sub>DSS</sub>	SS drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μA
		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 11	-	4.8	5.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	9.5	11.4	mΩ
Dynamic ch	naracteristics FET1 and FE	T2				
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 20 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V;	-	32.3	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	7.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	10.5	-	nC

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003aak979

4.5\_V

4 V

1

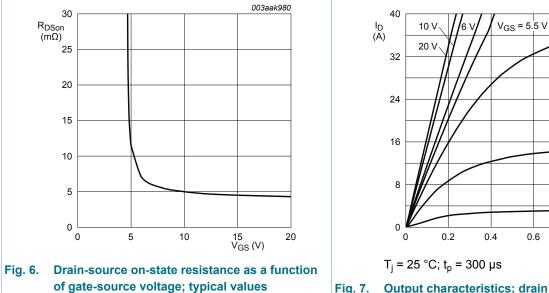
0.8 V<sub>DS</sub> (V)

0.6

5 V

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;		-	1657	2210	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	354	425	pF
C <sub>rss</sub>	reverse transfer capacitance			-	208	285	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 32 V; $R_{L}$ = 1.6 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 5 $\Omega$ ; $T_{j}$ = 25 °C; $I_{D}$ = 20 A		-	9.5	-	ns
t <sub>r</sub>	rise time			-	16	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	21	-	ns
t <sub>f</sub>	fall time			-	17	-	ns
Source-drai	n diode FET1 and FET2		1	1	1	1	
$V_{SD}$	source-drain voltage	$I_{S}$ = 15 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>		-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 5 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	25	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C		-	18	-	nC

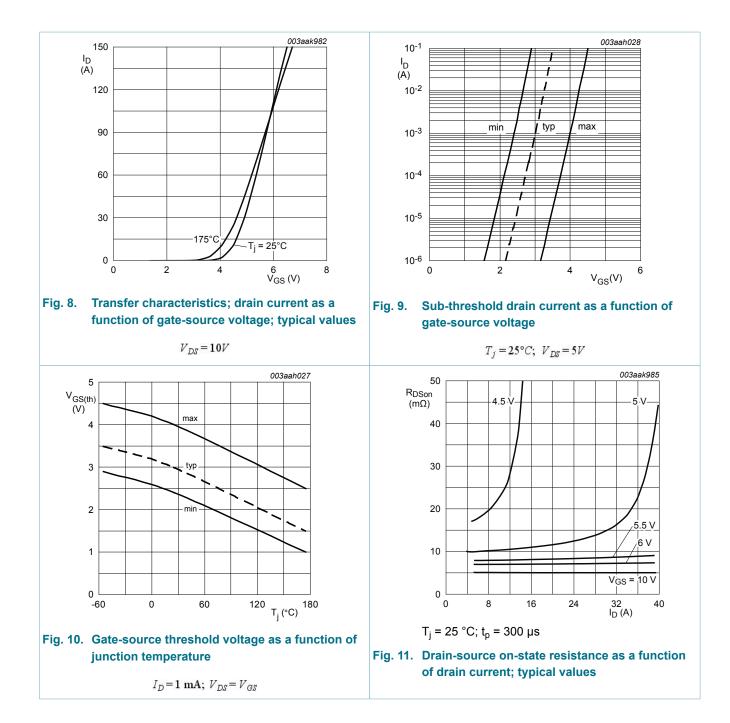


 $T_j = 25^{\circ}C; \ I_D = 20A$ 

Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

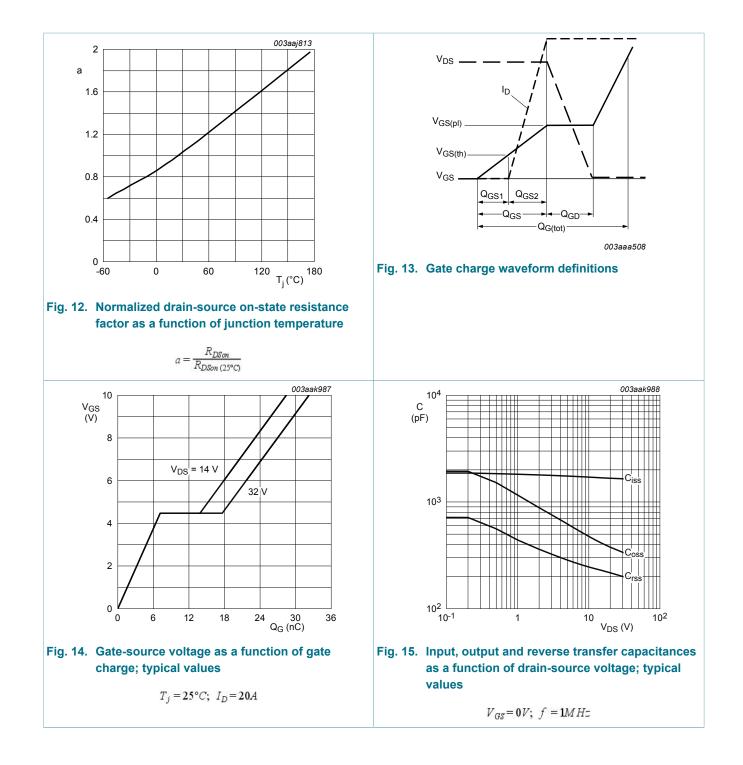
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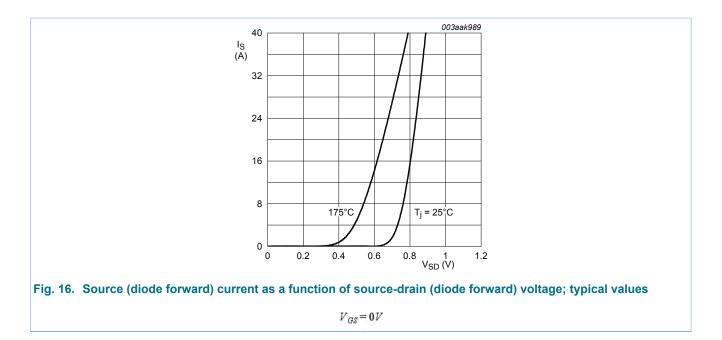


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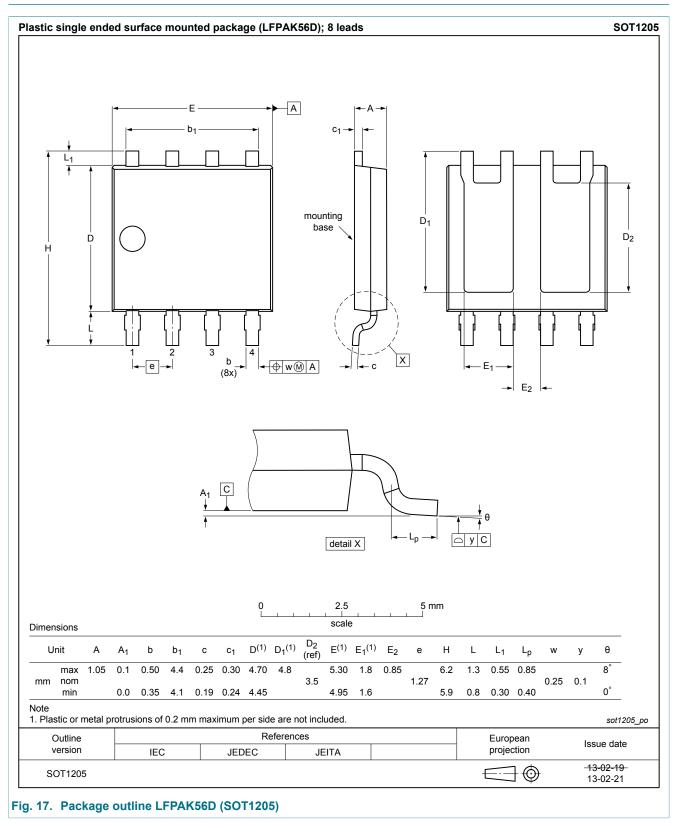
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### **11. Package outline**



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Product data sheet

#### Dual N-channel 40 V, 5.8 mΩ standard level MOSFET

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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